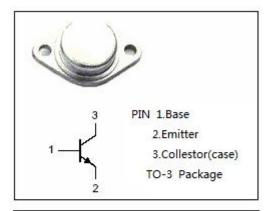


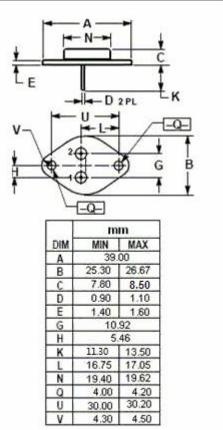
isc Silicon NPN Power Transistor

2N6573

DESCRIPTION

- Collector-Emitter Sustaining Voltage-: V_{CEO} = 250V(Min.)
- Fast Switching Speed
- High Current Capability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation





• Designed for converters, inverters, pulse-width- modulated regulators and a variety of power switching circuits.

APPLICATIONS

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	500	V
V _{CEO}	Collector-Emitter Voltage	250	V
VEBO	Emitter-Base Voltage	5	V
Ic	Collector Current-Continuous	10	А
Pc	Collector Power Dissipation@Tc=25 $^{\circ}$ C	125	W
TJ	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-65~150	°C



isc Silicon NPN Power Transistor

2N6573

ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

PARAMETER	CONDITIONS	MIN	MAX	UNIT
Collector-Emitter Saturation Voltage	I _C =3A; I _B = 0.3A		1	v
Base-Emitter On Voltage I _C = 7A; V _{CE} =3V			1.4	v
Emitter Cutoff Current V_{EB} = 8V; I _C = 0			0.1	mA
Collector Base Cutoff Current V _{CB} =500V; I _E = 0			0.1	mA
DC Current Gain	I _C =3A; V _{CE} =3V	20	60	
DC Current Gain	I _C = 7A; V _{CE} = 3V	7	21	
Current Gain-Bandwidth Product	I _C = 1A; V _{CE} = 10V	5		MHz
	Collector-Emitter Saturation Voltage Base-Emitter On Voltage Emitter Cutoff Current Collector Base Cutoff Current DC Current Gain DC Current Gain	Collector-Emitter Saturation Voltage $I_C=3A; I_B= 0.3A$ Base-Emitter On Voltage $I_C=7A; V_{CE}=3V$ Emitter Cutoff Current $V_{EB}=8V; I_C=0$ Collector Base Cutoff Current $V_{CB}=500V; I_E=0$ DC Current Gain $I_C=3A; V_{CE}=3V$ DC Current Gain $I_C=7A; V_{CE}=3V$	Collector-Emitter Saturation Voltage $I_C=3A; I_B=0.3A$ Base-Emitter On Voltage $I_C=7A; V_{CE}=3V$ Emitter Cutoff Current $V_{EB}=8V; I_C=0$ Collector Base Cutoff Current $V_{CB}=500V; I_E=0$ DC Current Gain $I_C=3A; V_{CE}=3V$ DC Current Gain $I_C=7A; V_{CE}=3V$	Collector-Emitter Saturation Voltage $I_C=3A; I_B=0.3A$ 1Base-Emitter On Voltage $I_C=7A; V_{CE}=3V$ 1.4Emitter Cutoff Current $V_{EB}=8V; I_C=0$ 0.1Collector Base Cutoff Current $V_{CB}=500V; I_E=0$ 0.1DC Current Gain $I_C=3A; V_{CE}=3V$ 2060DC Current Gain $I_C=7A; V_{CE}=3V$ 721

Switching times

Ton	On Time	I _C = 7Α; I _B =1.4Α,	1	μ S
t _{off}	Off Time	IC- / A, IB- 1.4A,	3.2	μ S

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